

Appl. No. 10/708,152  
Amdt. dated July 25, 2005  
Reply to Office action of July 05, 2005

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

- 1 (currently amended): A method for fabricating a fluid injection head  
5 structure comprising steps of:  
providing a substrate;  
forming at least one bubble generator on the substrate;  
forming at least one functional device;  
forming a first conductive trace, ~~which is composed of a poly-silicon layer~~ the first  
10 conductive trace formed of poly-silicon; and  
forming a second conductive trace, which is used to electrically couple  
the functional device with the bubble generator, and also serves to  
couple the functional device with the first conductive trace.
- 15 2 (original): The method of claim 1 wherein the method further  
comprises forming a contact layer positioned between the first  
conductive trace and the second conductive trace to electrically  
couple the first conductive trace with the second conductive trace.
- 20 3 (original): The method of claim 1 wherein the second conductive  
trace comprises a pad.
- 4 (original): The method of claim 1 wherein the method further  
comprises a step of forming a dielectric layer between the first  
25 conductive trace and the second conductive trace.
- 5 (original): The method of claim 1 wherein the functional device is a  
transistor comprising a source, a drain and a gate.

Appl. No. 10/708,152  
Amdt. dated July 25, 2005  
Reply to Office action of July 05, 2005

6 (original): The method of claim 5 wherein the transistor is a metal oxide semiconductor field effect transistor (MOSFET) and the gate is composed of a poly-silicon layer.

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7 (original): The method of claim 1 wherein the gate and the first conductive trace are formed in a same photo-etching process (PEP).

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8 (original): The method of claim 1 wherein the material of the second conductive trace is any one of aluminum, gold, copper, tungsten, alloys of aluminum-silicon-copper, and alloys of aluminum-copper.

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9 (original): The method of claim 1 wherein the bubble generator comprises a first bubble generating device and a second bubble generating device positioned adjacent to a corresponding orifice on a corresponding chamber, wherein when the chamber is full of fluid, the first bubble generating device generates a first bubble, and then the second bubble generating device generates a second bubble to eject the fluid from the chamber through the orifice.

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10 (original): The method of claim 9 wherein the first bubble serves as a virtual valve, restricts flow of fluid out of the chamber.

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11 (original): The method of claim 1 wherein the method further comprises the steps of:

forming a dielectric layer on the substrate;

etching the substrate and the dielectric layer to form a manifold and at

Appl. No. 10/708,152  
Amdt. dated July 25, 2005  
Reply to Office action of July 05, 2005

least one chamber connected to the manifold such that fluid can  
flow through the manifold to the chamber; and  
forming at least one orifice positioned adjacent to the corresponding  
bubble generator, which is connected to the chamber for ejecting  
5 the fluid.

12 (original): The method of claim 11 wherein the method further  
comprises a step of:  
forming a low stress layer, wherein the bubble generator is formed  
10 on the low stress layer.

13 (original): The method of claim 11 wherein the injection head is  
used as a print head of an inkjet printer, the manifold is connected  
to an ink cartridge, and the fluid is the ink of ink cartridge.  
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14 (currently amended): The method of claim 1 wherein at least one  
layer of the functional device is formed on ~~[[the]]~~ a same poly-silicon layer as  
the first conductive trace.

20 15 (currently amended): The method of claim 6 wherein the gate of the  
MOSFET is formed on ~~[[the]]~~ a same poly-silicon layer as the first conductive  
trace.